SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

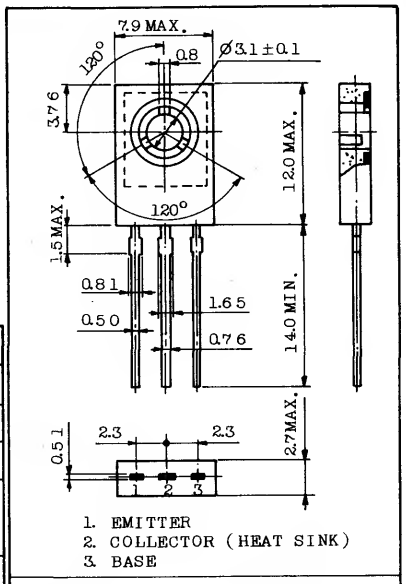
2SC3335

HIGH VOLTAGE SWITCHING APPLICATIONS.
COLOR TV CHROMA OUTPUT APPLICATIONS.

FEATURES:

. High Voltage : V_{CEO}=250V
. Low Cre : 2.0pF(Max.)
. Complementary to 2SA1322

Unit in mm



1. EMITTER
2. COLLECTOR (HEAT SINK)
3. BASE

JEDEC	TO-126
EIAJ	—
TOSHIBA	2-8F1A

Weight : 0.72g
Mounting Kit No. AC46C

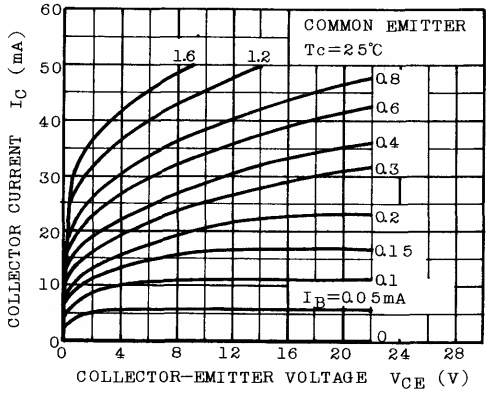
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	250	V
Collector-Emitter Voltage		V_{CEO}	250	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	50	mA
	Peak	I_{CP}	100	
Base Current		I_B	20	mA
Collector Power Dissipation	Ta=25°C	P_C	1.2	W
	Tc=25°C		10.0	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55 ~ 150	°C

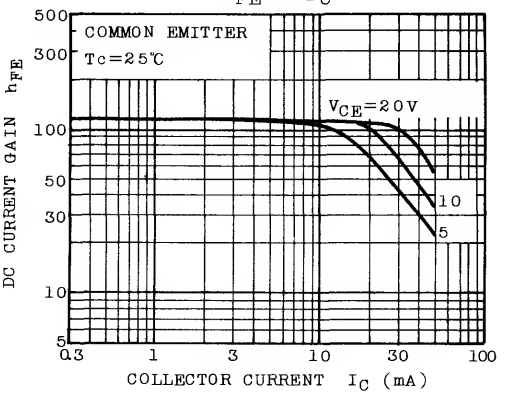
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=200V, I_E=0	-	-	1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	250	-	-	V
DC Current Gain	h_{FE}	V_{CE}=20V, I_C=25mA	50	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=10mA, I_B=1mA	-	-	1.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=20V, I_C=25mA	-	0.75	-	V
Transition Frequency	f_T	V_{CE}=10V, I_C=10mA	60	100	-	MHz
Reverse Transfer Capacitance	Cre	V_{CB}=30V, I_E=0, f=1MHz	-	-	2.0	pF

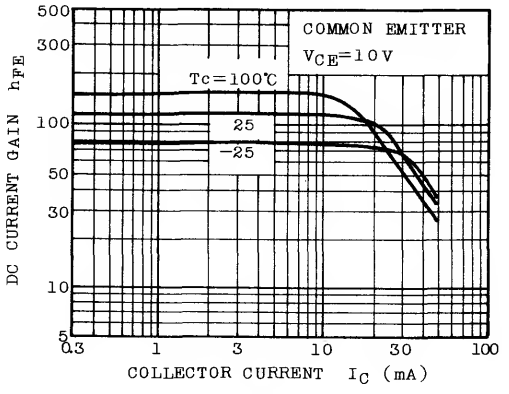
$I_C - V_{CE}$ (LOW VOLTAGE REGION)



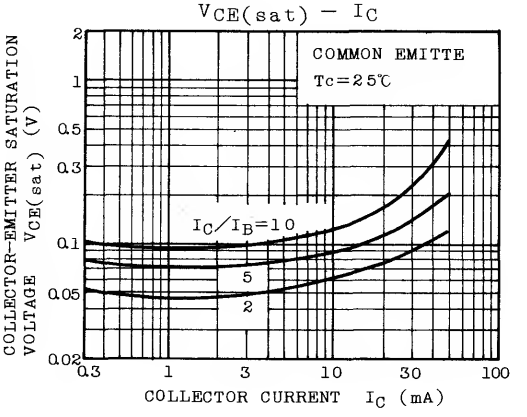
$h_{FE} - I_C$



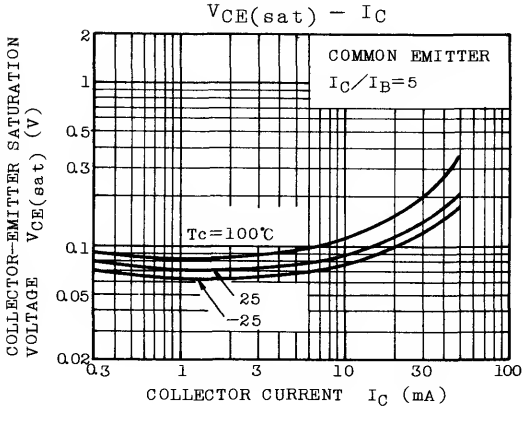
$h_{FE} - I_C$



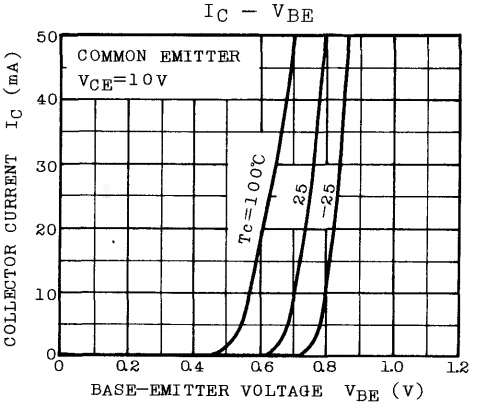
$V_{CE(sat)} - I_C$



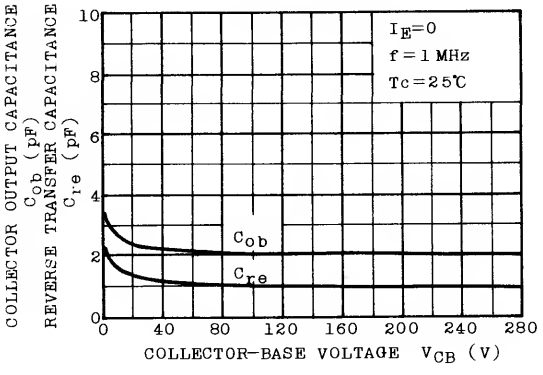
$V_{CE(sat)} - I_C$



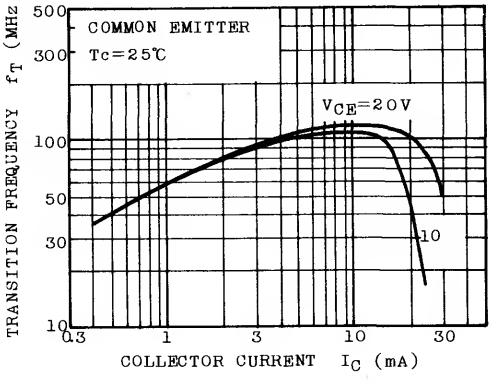
$I_C - V_{BE}$



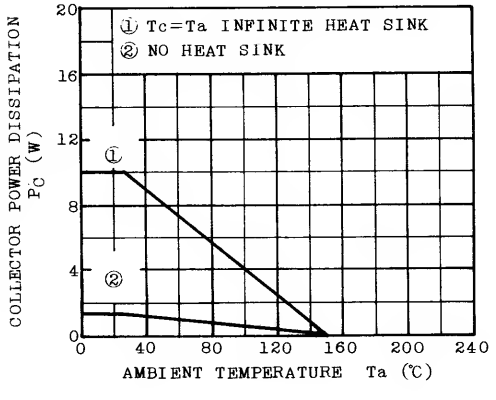
C_{ob}, C_{re} – V_{CB}



f_T – I_C



P_C – Ta



SAFE OPERATING AREA